

# Fitting DFM in Your Design Flow

2007 Electronic Design Process Workshop

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# Purpose

- **Clarify the buzz words – DFM & DFY**
  - **The origins of DFM**
  - **Relationship between DFM & DFY**
- **Explain the business significance**
- **DFM Methods in use today**
  - **Where the methods are used**
  - **How the methods are used**
- **Future DFM Challenges & Opportunities**

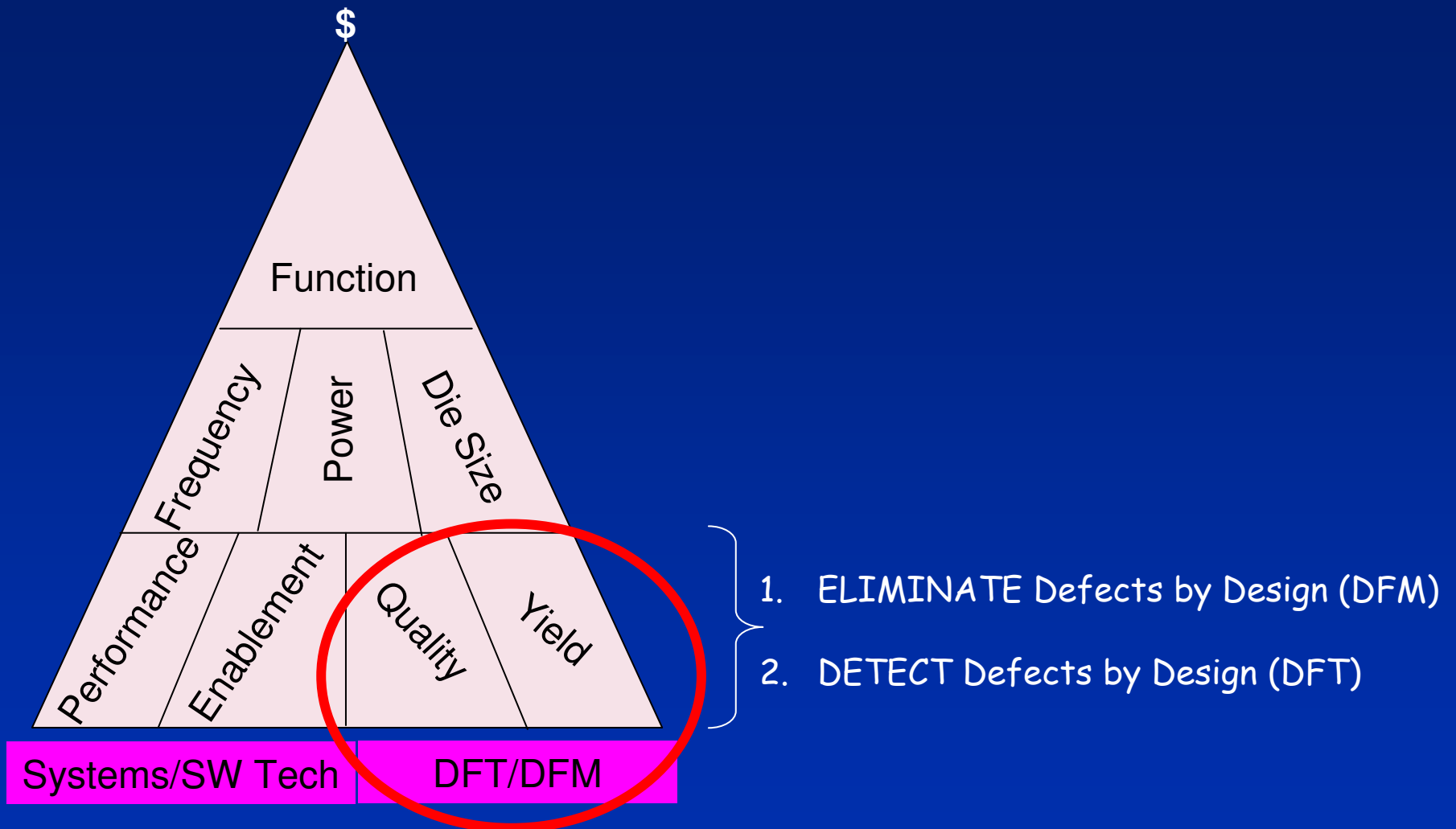
# Outline

- **DFM Origins**
- **How DFM is understood today**
  - **Taxonomy & Terminology**
- **DFY in Practice**
  - **DRM, Metrics, Measurement**
  - **DFY in Libraries**
  - **DFY in SOC – RTL Synthesis, Place & Route**
  - **DFY in SOC – Chip Optimization, LVS/DRC**
- **Future DFM Methods**
- **Conclusions**

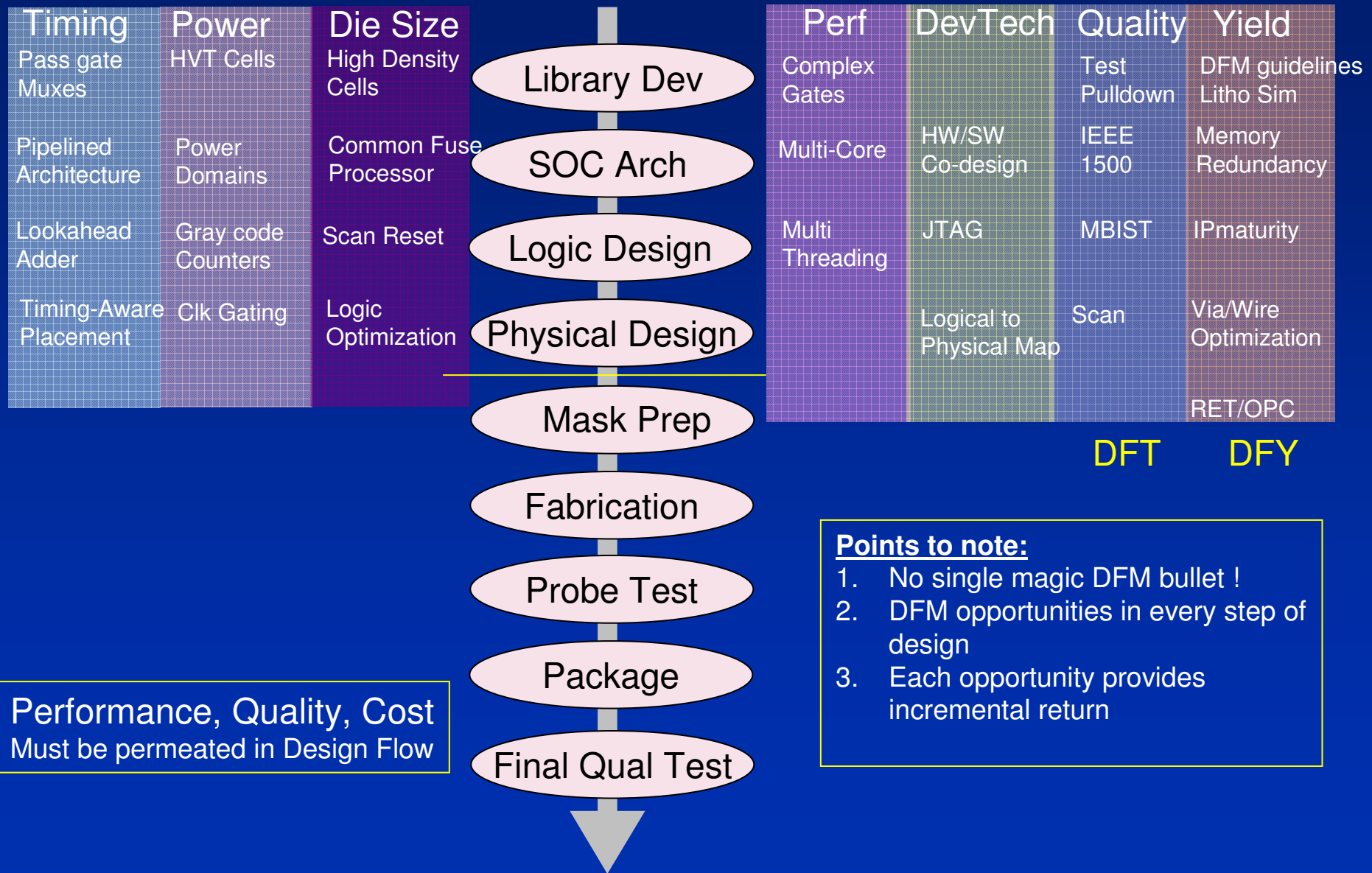
# Acknowledgements

- **DFM Team**: Ken Danti, Scott Hector, Paula Nguyen, Lionel Riviere-Cazau, Matt Thompson, Ruiqi Tian, Carla Thomas, Peter Turner
- **Business Groups**: Chris Ahrens, Ezra Baruch, Mahboob Rashed, Tom Thomas, Ravi Vaidyanathan, Jeff Warner, Michael Zimin
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- **Management**: Joe Pumo, Ross Hirschi, Suresh Venkatesan, Dirk Wristers
- **EDA Vendors**: Cadence Design Systems, Mentor Graphics Corporation

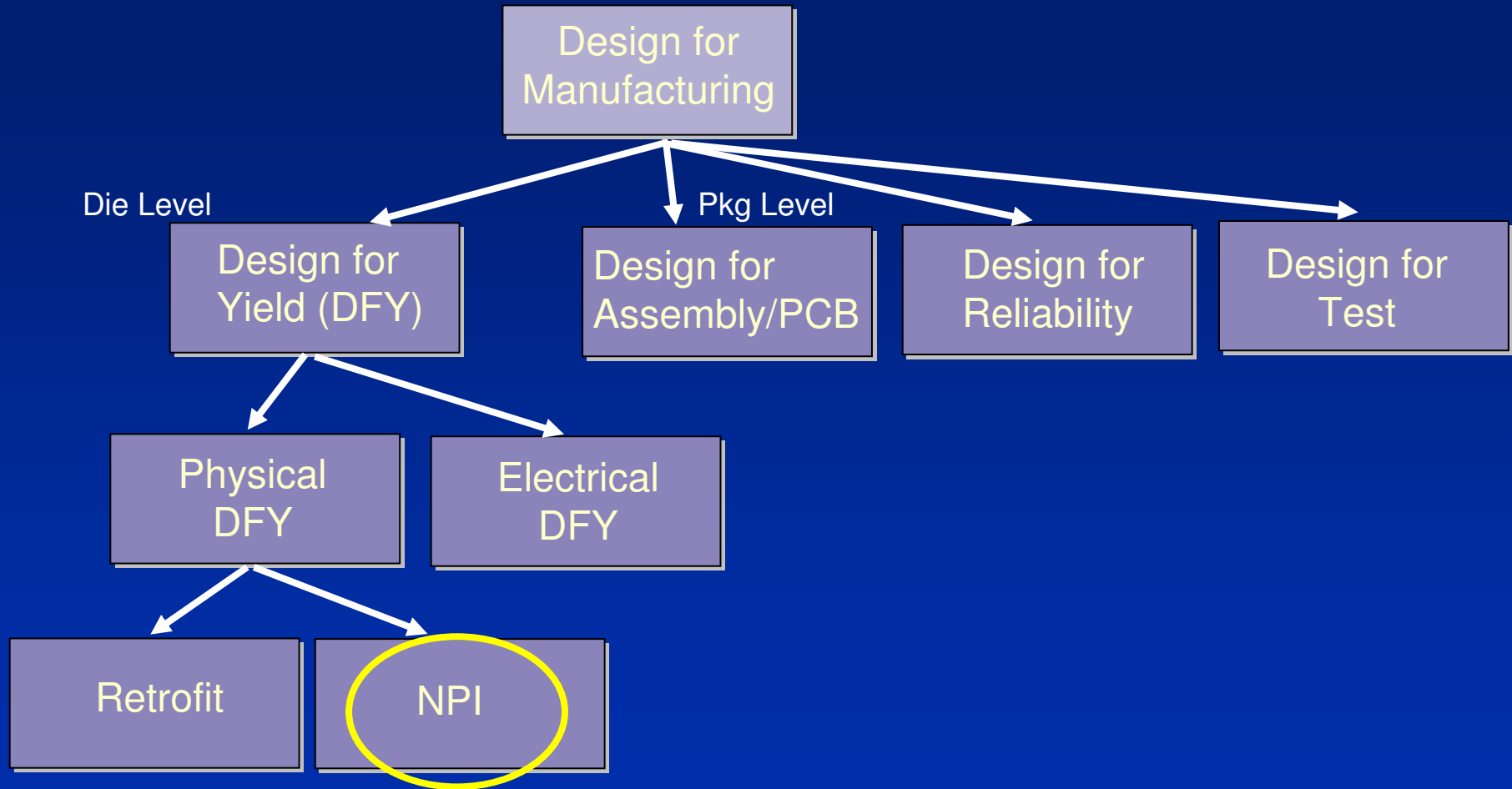
# Selling a Chip – What to consider during design



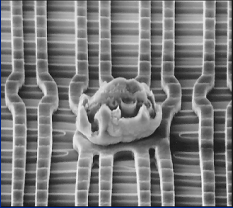
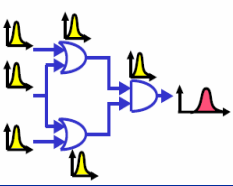
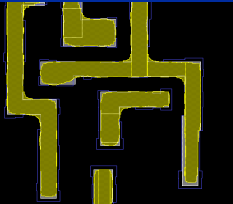
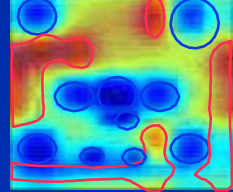
# Design Technology Differentiators



# The World of DFM

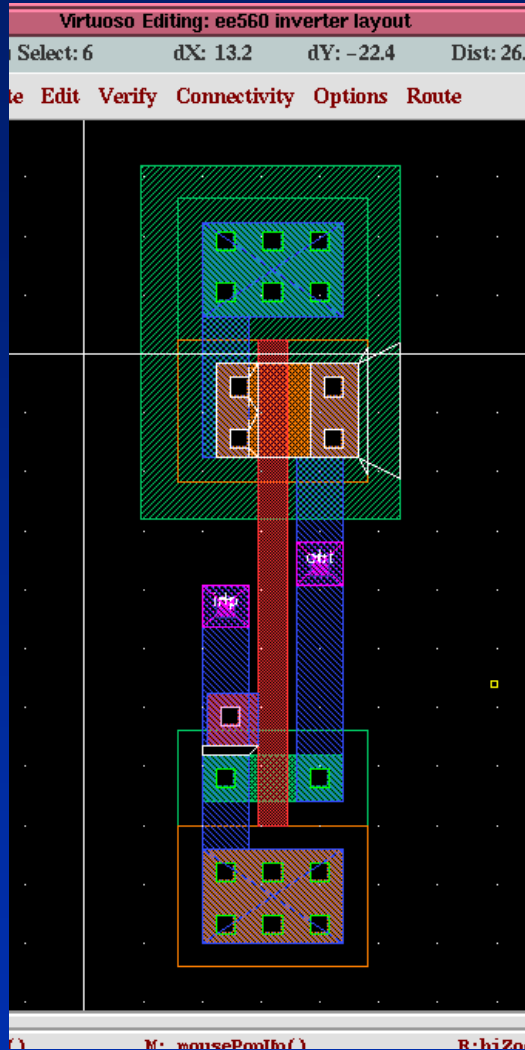


# Techniques for Improving Yield

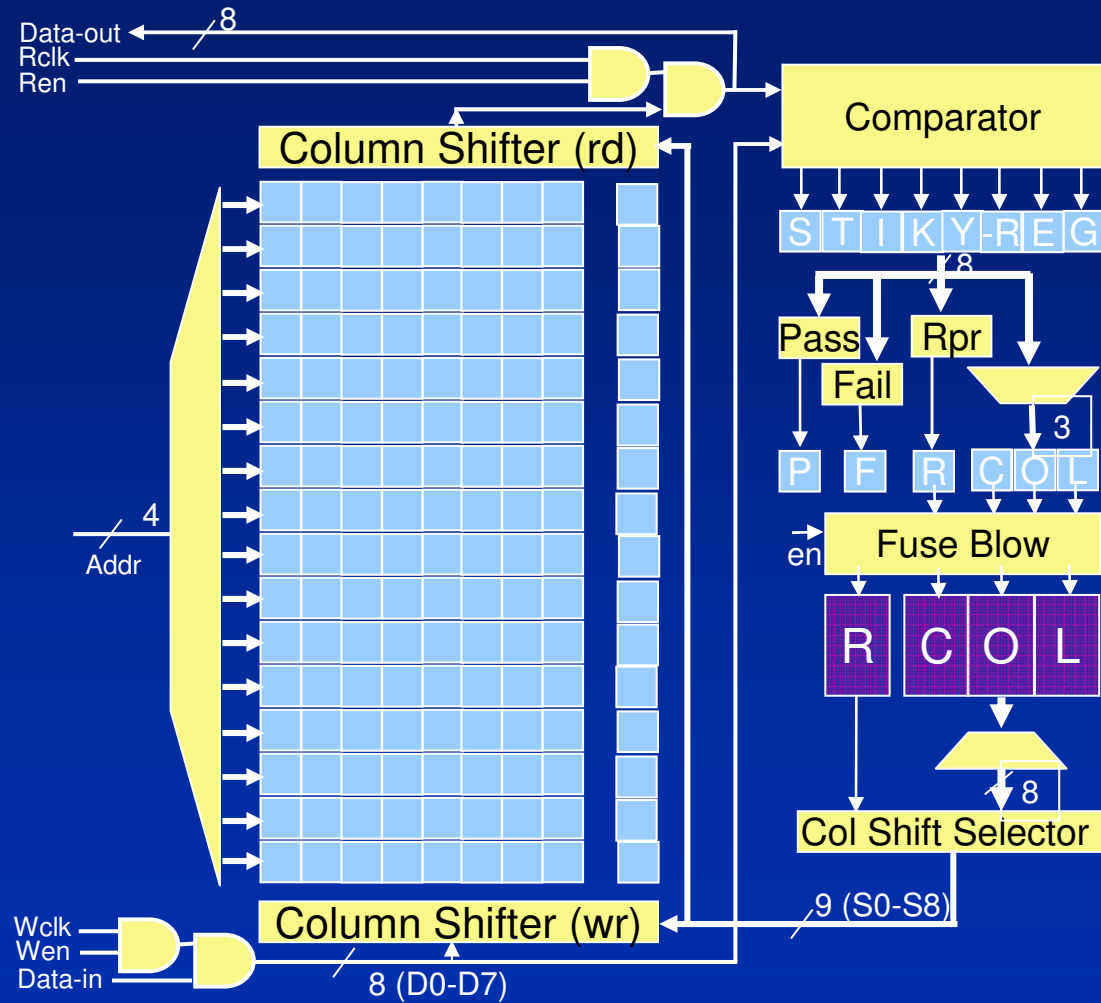
Defect source	Description	DFY Countermeasures
 <p>Random Physical</p>	<ul style="list-style-type: none"> <li>• Metal/poly shorts and opens</li> <li>• Contact/via voids</li> <li>• Missing or extra pattern</li> <li>• Stress cracks</li> </ul>	<ul style="list-style-type: none"> <li>• Increase poly pitch and spacing to contacts</li> <li>• Contact/via redundancy and reduction</li> <li>• Wire widening and spreading</li> <li>• ↑ area of metal/active islands</li> </ul>
 <p>Device variation</p>	<ul style="list-style-type: none"> <li>• <math>L_{\text{eff}}</math> variation (gate length, dopants, oxide thickness)</li> <li>• Devices not matching models due to local layout (stress, well and pattern proximity)</li> </ul>	<ul style="list-style-type: none"> <li>• Rule-based changes to layout to mitigate proximity effects (poly and active corners, poly pitch, contact spacing to gate)</li> <li>• Statistical device &amp; timing models</li> </ul>
 <p>Lithography capability &amp; variation</p>	<ul style="list-style-type: none"> <li>• Small focus/exposure window</li> <li>• Bridging and pinching</li> <li>• Corner rounding and pullback</li> <li>• Overlay errors</li> </ul>	<ul style="list-style-type: none"> <li>• Lithography simulation (using OPC model) to find &amp; remove hot spots</li> <li>• Jog elimination</li> <li>• Via enclosure optimization</li> </ul>
 <p>Topography due to CMP</p>	<ul style="list-style-type: none"> <li>• Non-planar topography due to pattern density variation</li> <li>• Dishing &amp; erosion</li> <li>• Oxide thickness</li> </ul>	<ul style="list-style-type: none"> <li>• Rule-based tiling</li> <li>• CMP-model-driven tiling and extraction</li> </ul>



# DFM is not new

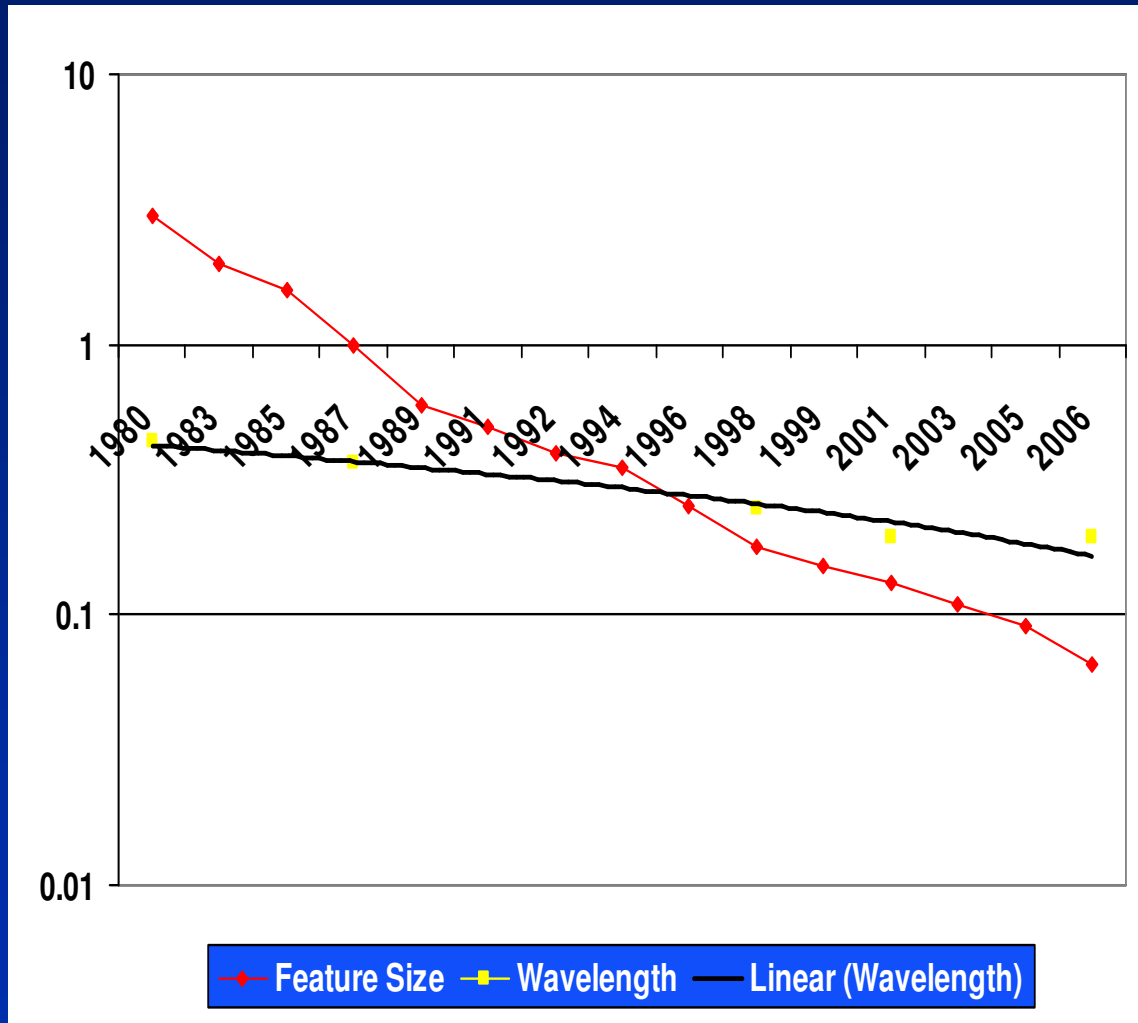


**DRC**



**Column Redundancy**

# DFM – Why the *Buzz* now ?

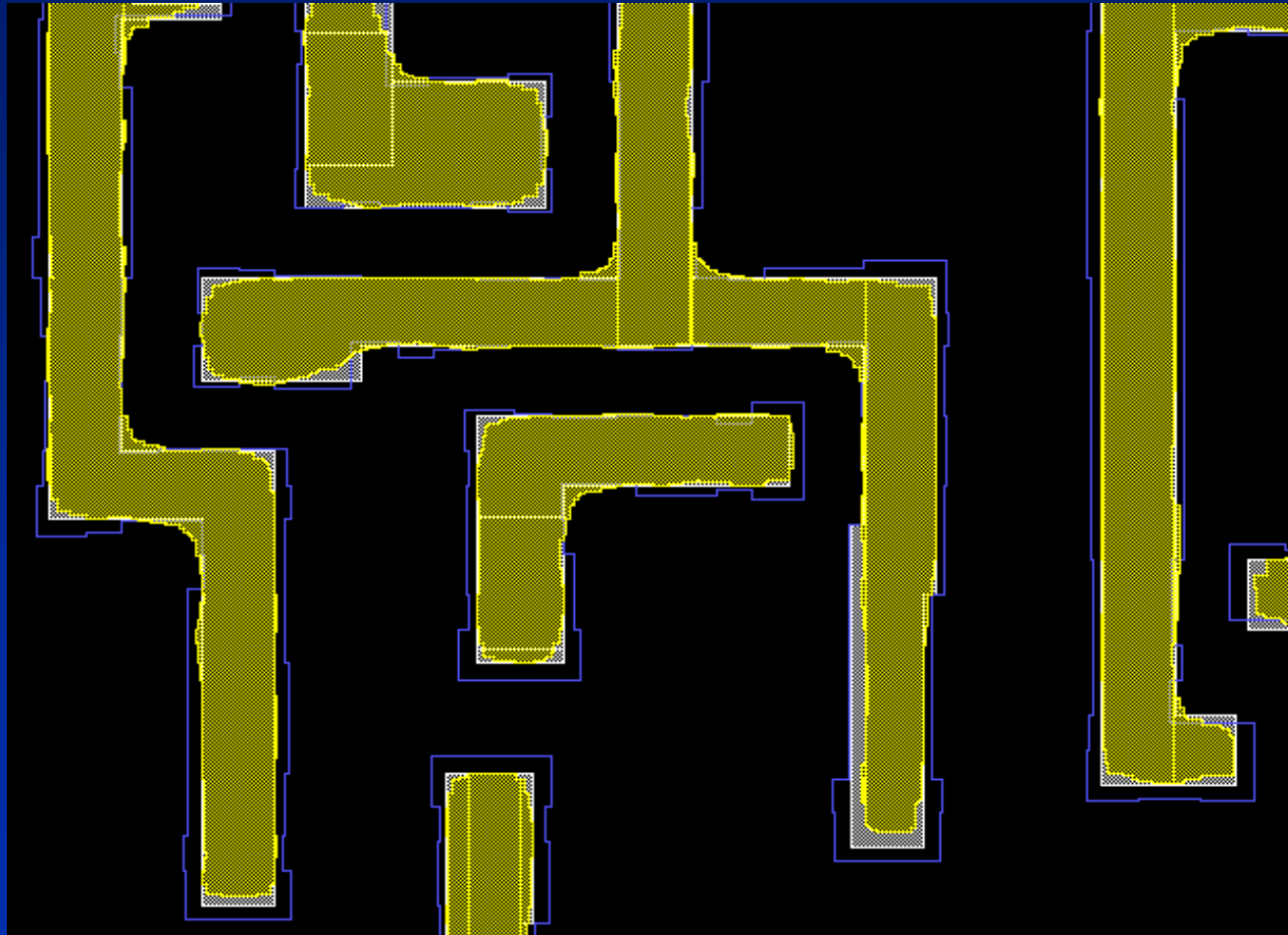


**193nm Stepper**

*Courtesy: ASML*

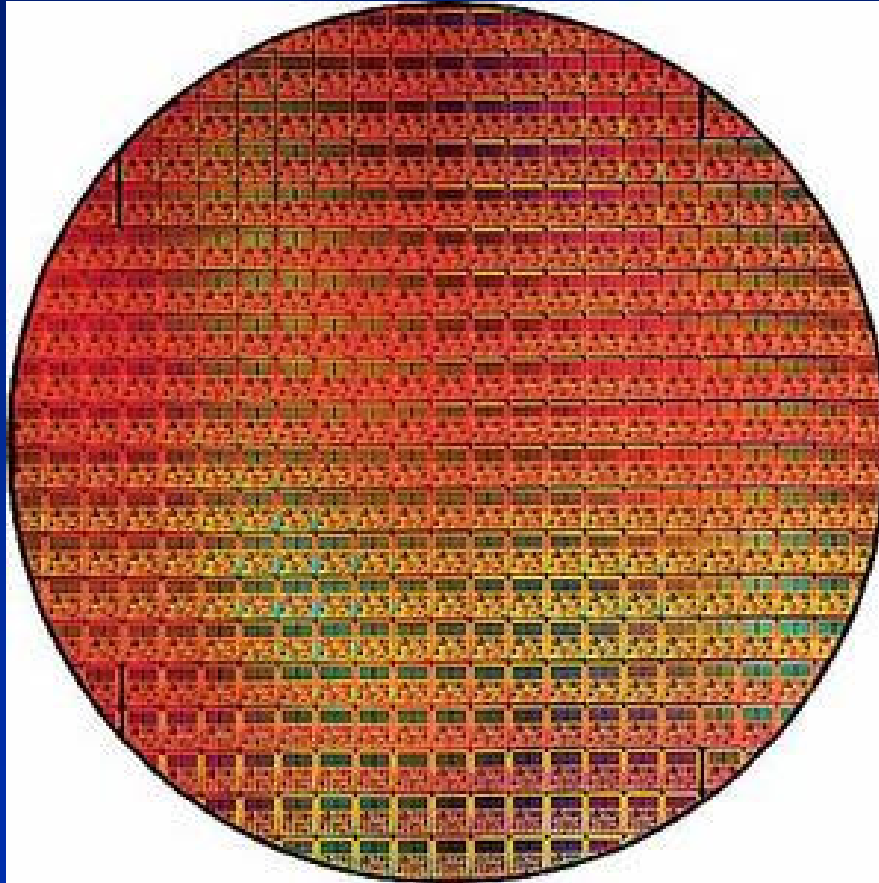
**Feature Size Smaller Than Wavelength**

# DFM – Lithography Variation



White - Original Drawn. Green - Manufactured. Blue – Corrected Drawn

# DFM – Business Case



Process: 90nm Bulk  
Layers: 6

Masks: 26

Wafer Size: 300 mm

Wafer Cost: \$3030

Wafer Sold: \$5000

Volume: 30K/month

Yield Increase: 1%

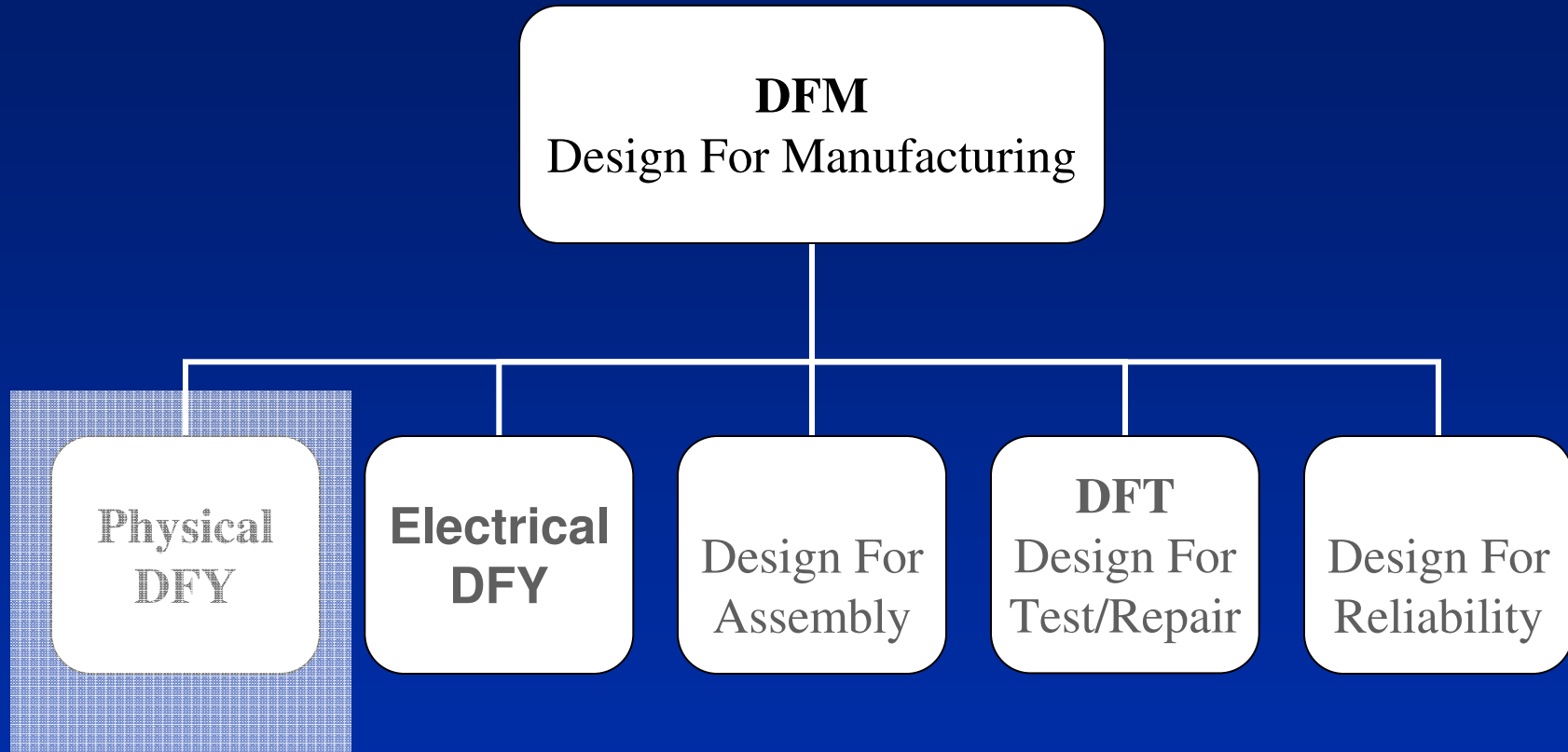
Revenue increase:

**\$1.5M/month**

Test Coverage: 99%

DPM improvement: **7%**

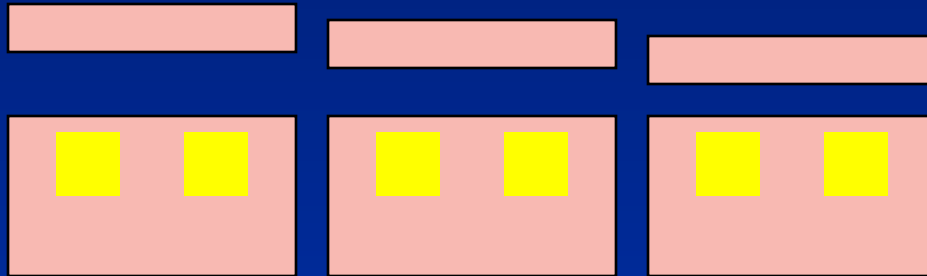
# DFM and Physical DFY



# DFY Test Vehicles – Examples

- Example:

- Wide metal enclosure of via

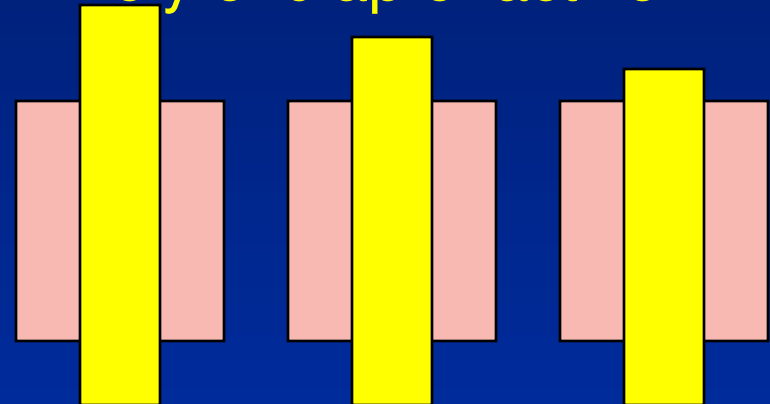


Better yield

At DRM

- Example:

- Poly endlap of active

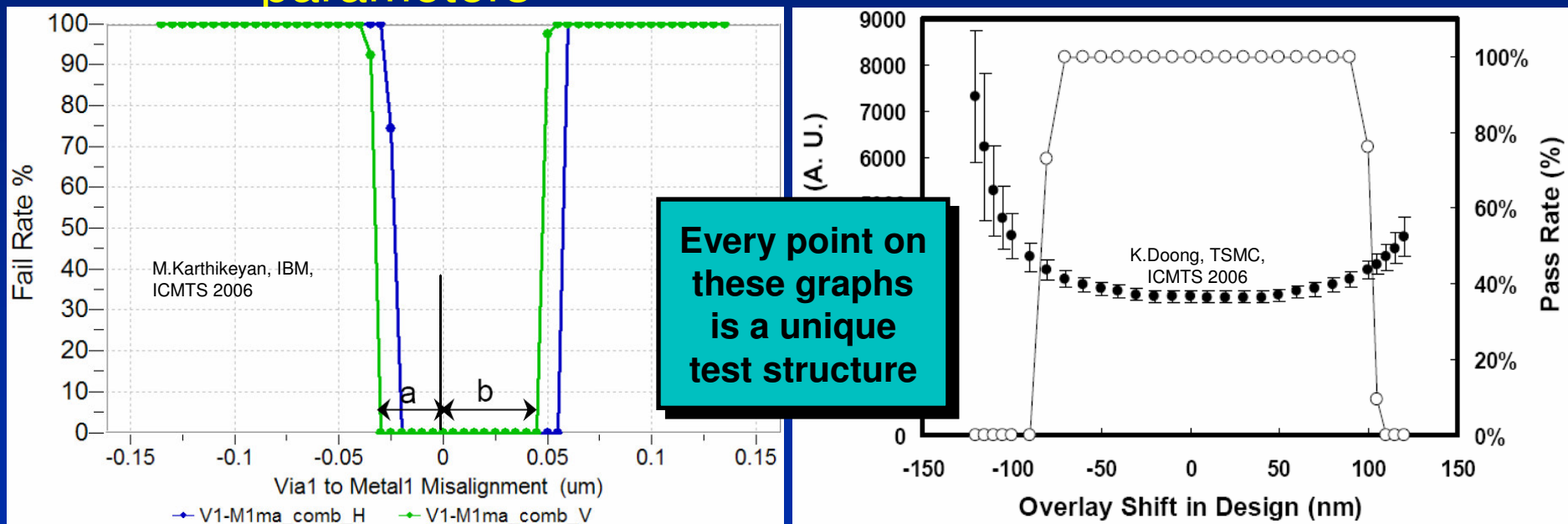


Better yield

At DRM

# DFY Test Vehicles – Reporting

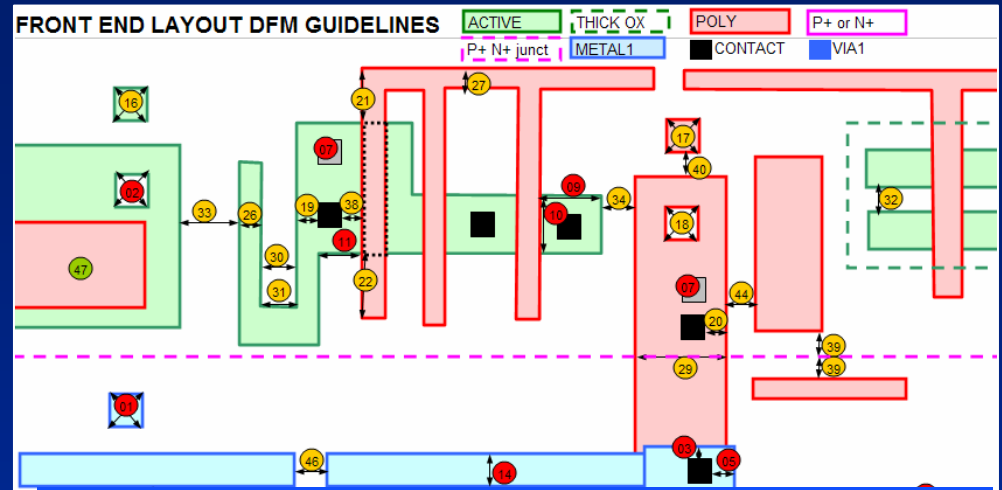
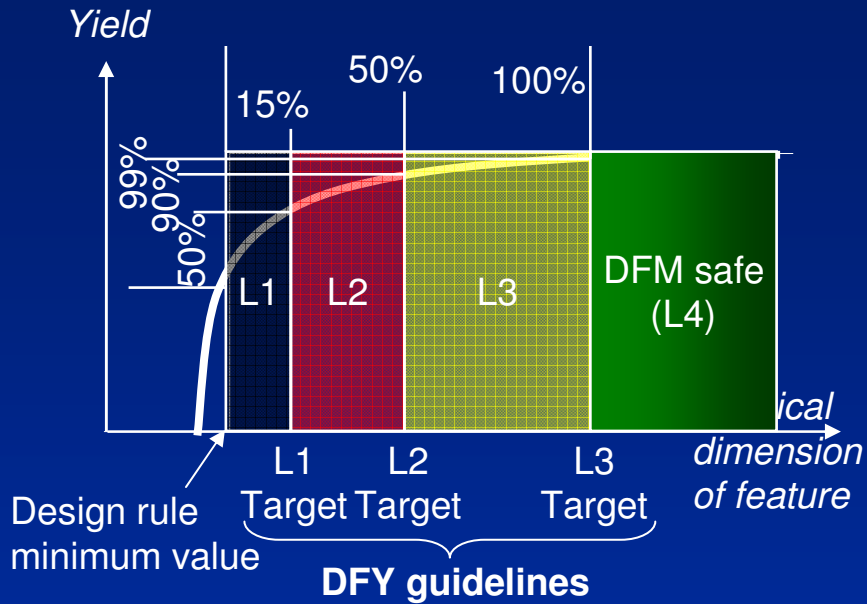
- Manual reports
  - Graphs showing yield as a function of one or more parameters



- Yield modeling
  - Table to feed yield models

*Courtesy: Technology Validation Group, Brad Smith*

# DFY in Practice – DRM, Metrics



Guidelines established for many aspects of front end and backend layout that affect yield

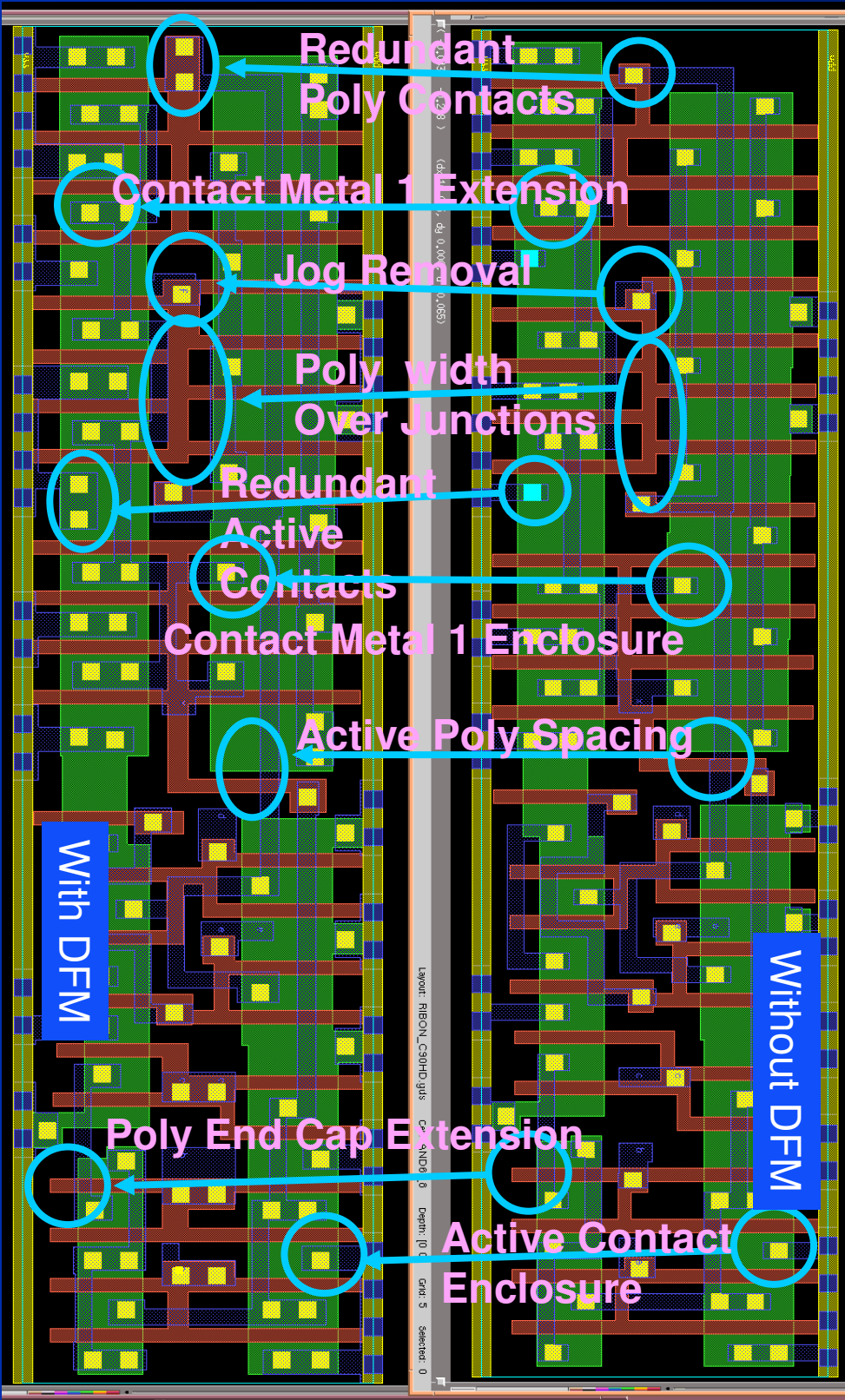
Re	Naming	Rules Criticality	DRM reference rules	L1	L2	L3	Comments
1	AR1_M1	1HC	Min Area M1.A.1	0.042	0.046	0.050	0.060
2	AR3_OD	1HC	Min enclosedArea OD.A.2	0.085	0.093	0.107	0.200
3	EN1_M1.CO	1HC	Via/Contact Min enclos M1.EN.1	0	0.005	na	0.01
4	EN1_M1.VIA1	1HC	Via/Contact Min enclos VIA1.EN.1	0	0.005	na	0.01
5	EX1_M1.CO	1HC	Via/Contact Min enclos M1.EX.1	0.04	0.045	0.05	0.06
6	EX1_M1.VIA1	1HC	Via/Contact Min enclos VIA1.EX.1	0.04	0.045	0.05	0.06
7	RE1_CO.OD	1HC	Redundability	2x	na	na	2x
7	RE1_CO.PO	1HC	Double if possible, with	2x	na	na	2x
8	RE1_VIA1	1HC	back up as far as possible	2x	na	na	2x

Example of guidelines values

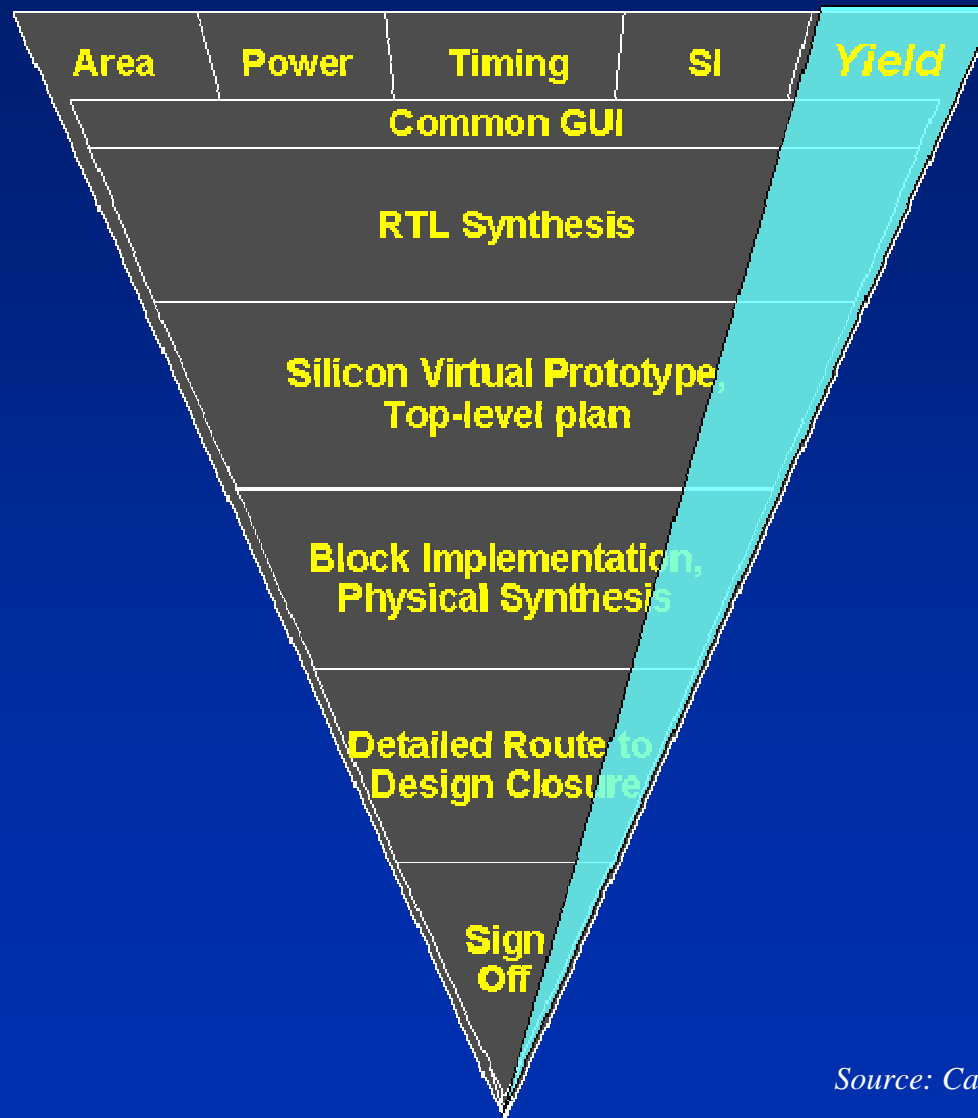
Source: Lionel Riviere-Cazaux



# DFY in Practice - Libraries



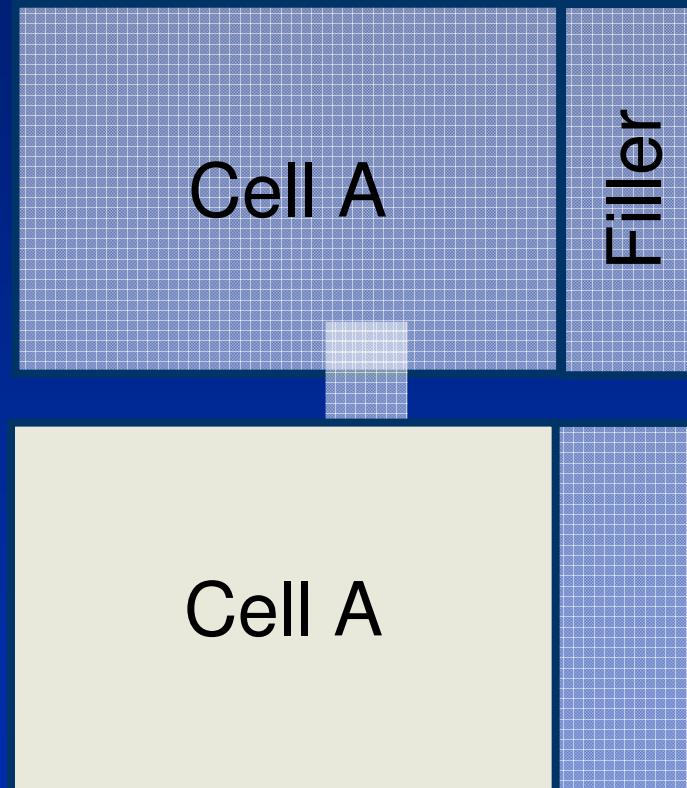
# DFY in Practice - SOC



*Source: Cadence Design Systems*

# DFY in Practice - Stretched StdCells

Place & Route blocks use up to 30% filler cells

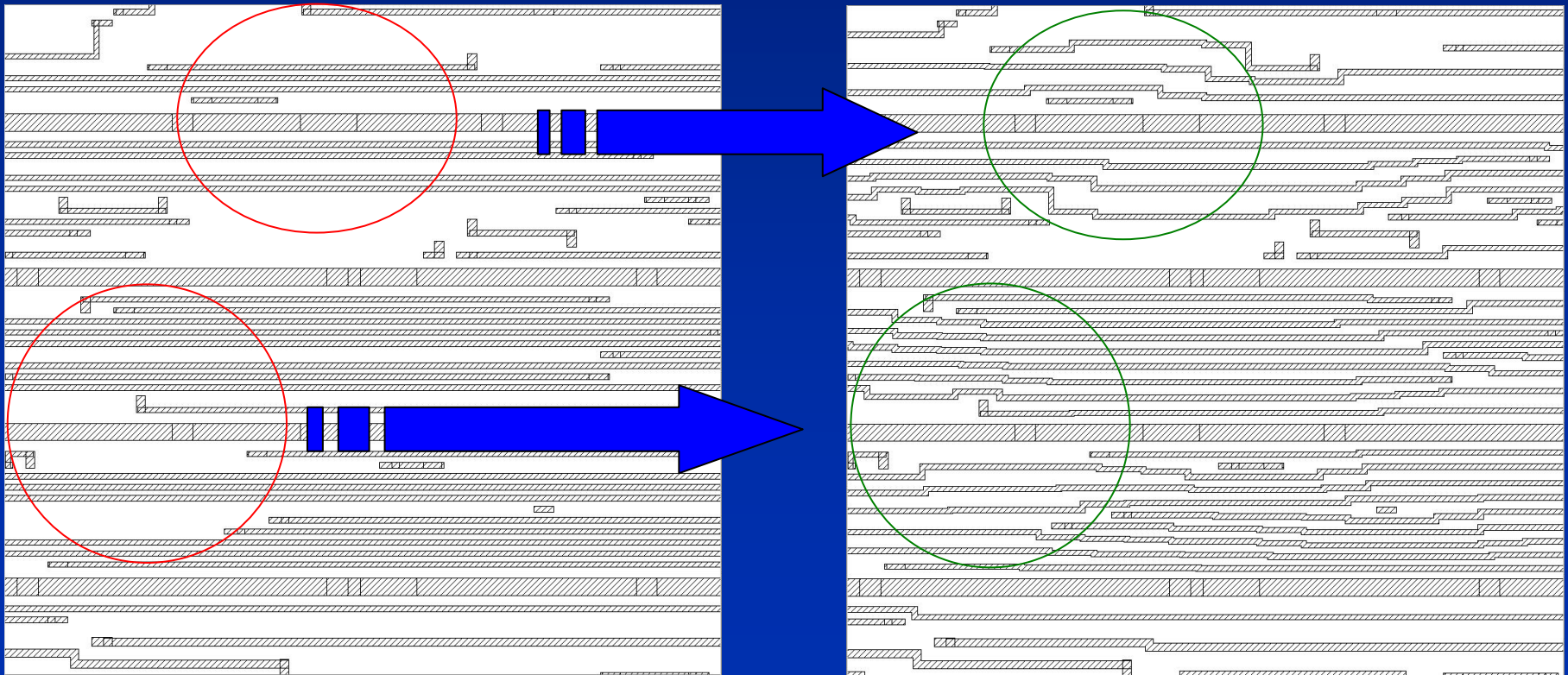


Swap regular cells...

...by stretched cells

# DFY in Practice - Wire Spreading

- Wire spreading goal is to seek congested minimum space areas and spread the wires to reduce shorts.

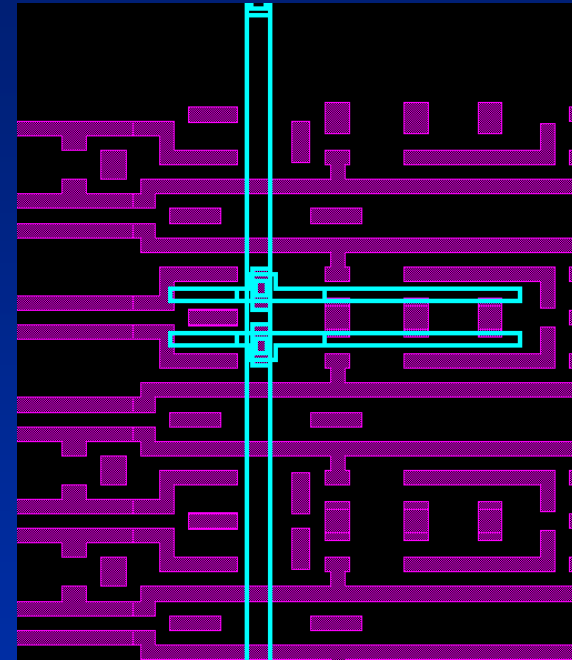




# DFY in Practice – Avoiding Overkill



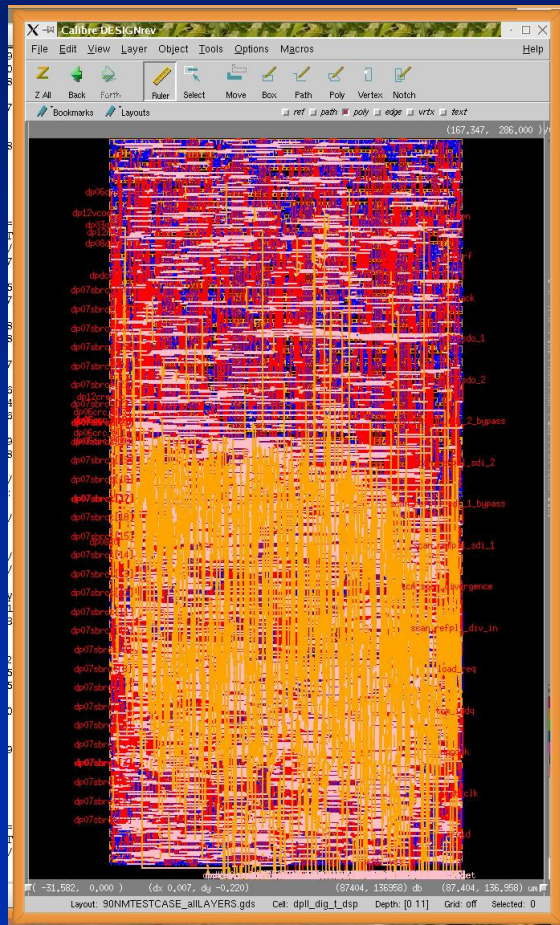
**Potential Bridging?**



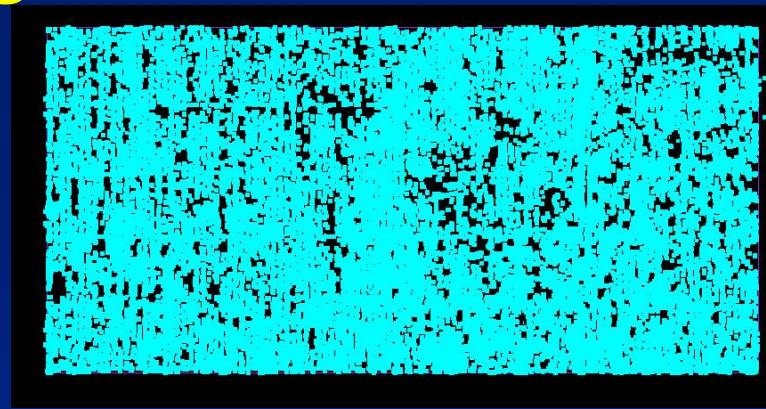
**Same Electrical Net**

*Source: Andy Espensceid*

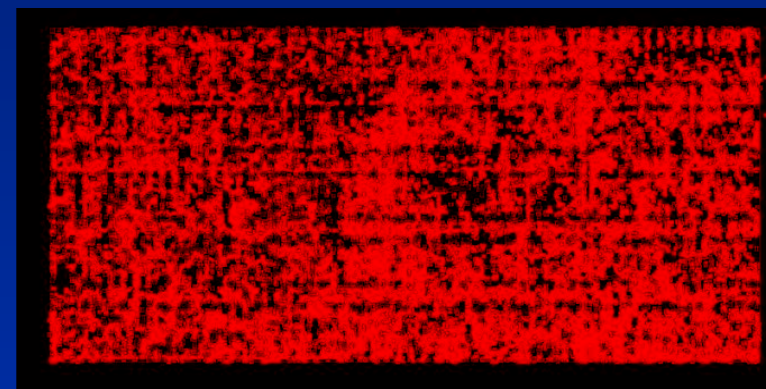
# DFY - Results



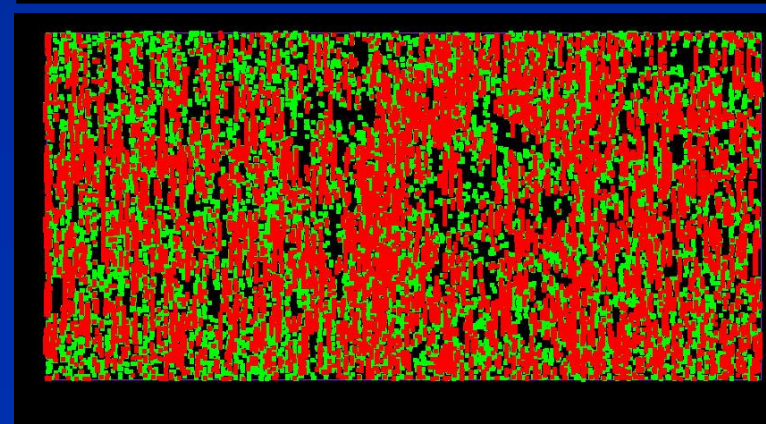
90nm, 6 layer Process



DRC  
Clean

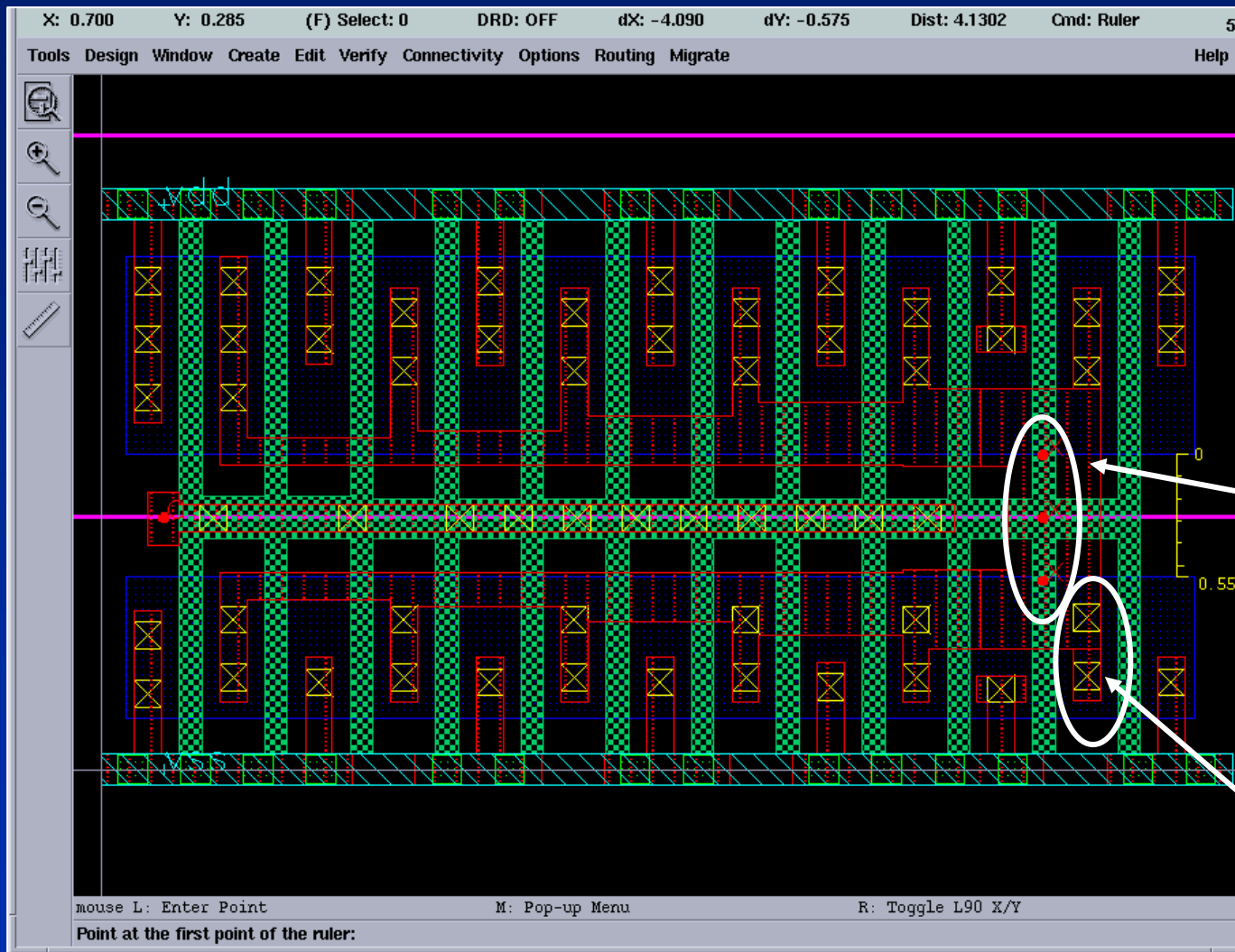


DFM  
Check



DFM Fix  
Area Neutral

# Electrical DFY



M1 Track Available

Single Vertical Track to O/P

Optimal Finger Sizing

Source: Michael Zimin

# Electrical DFY

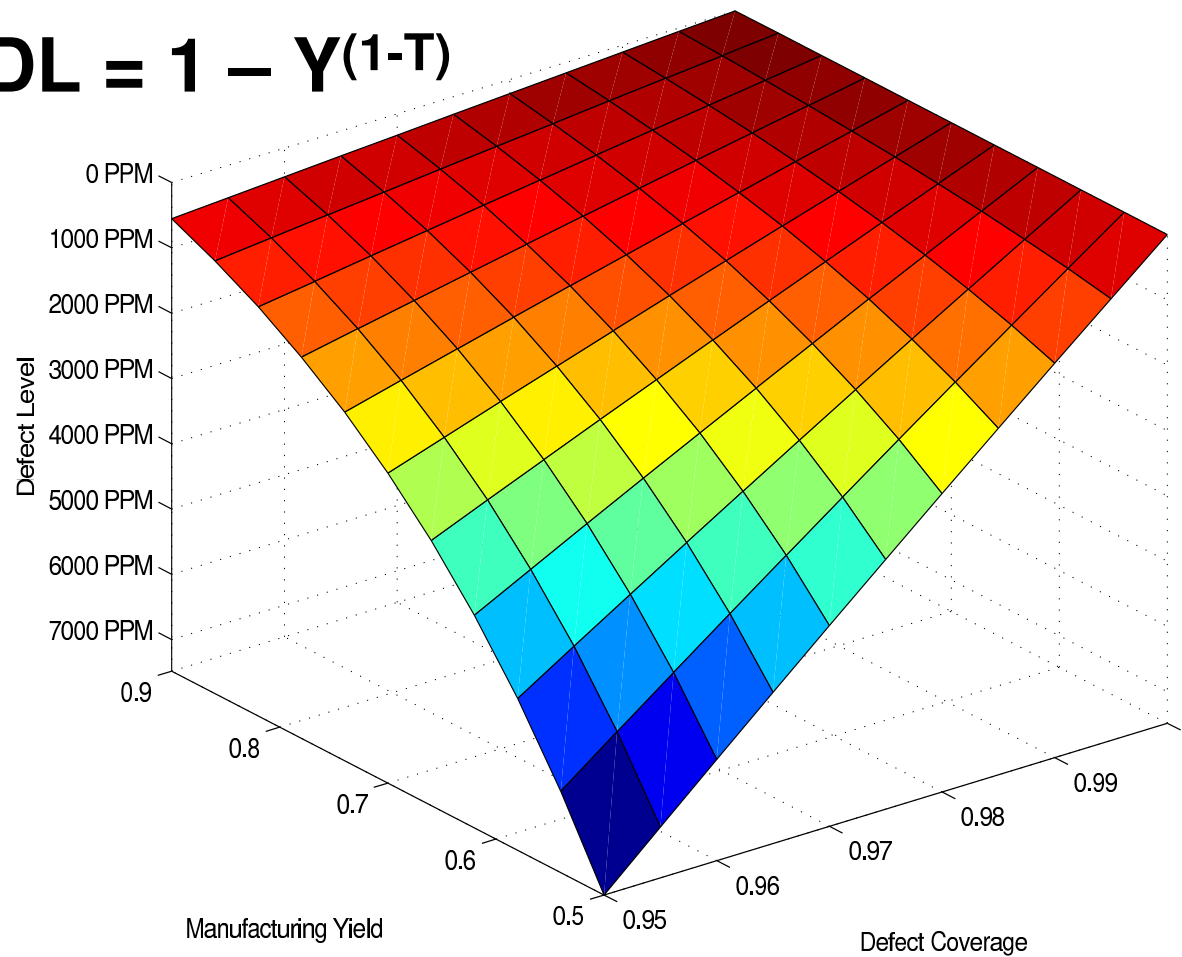
- **Physical defects can be seen. Electrical defects cannot be seen.**
- **However Electrical Operation is affected which leads to Yield loss**
- **Electrical DFY Opportunities**
  - P/N Ratios
  - Using M2 for Clock inside FF
  - Making multiple vertical tracks available
  - Using M1 for power (in addition to M2)



# DFY & DFT Nexus

Defect Level vs Manf. Yield & Defect Coverage (Agrawal Model with  $n_0 = 3.5$ )

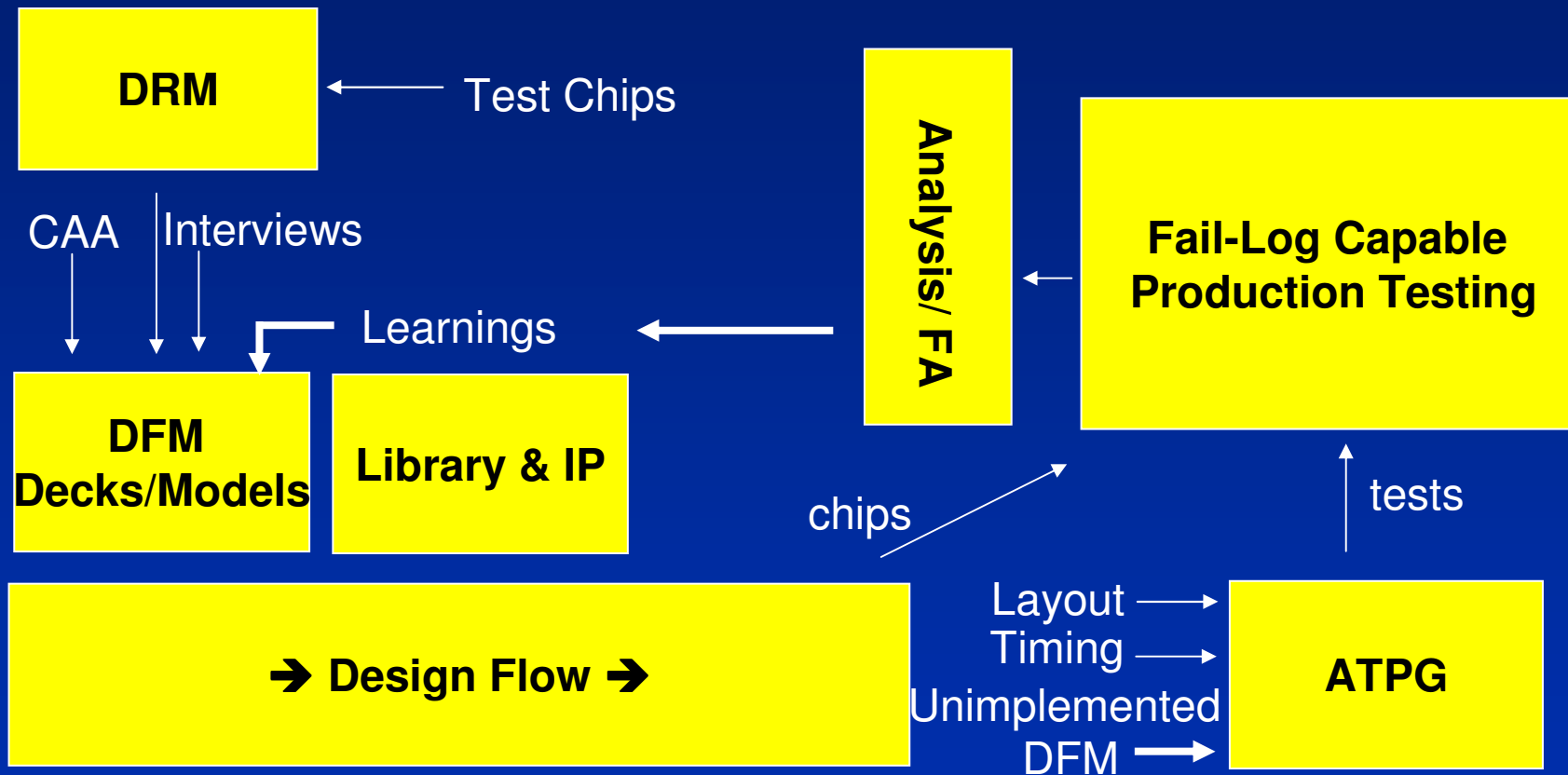
$$DL = 1 - Y(1-T)$$



Y = Yield  
T = Test Cov  
DL = Defect Level

Source: Williams & Brown '81

# DFY & DFT Nexus



# DFM – Future Opportunities

- **Standard Definitions**
- **Integrating into Design Flow**
- **Model Based vs Rule Based**
- **Electrical DFY**
- **DFY and DFT helping each other**

# Conclusions

- **DFM is an extension of DRC**
- **Physical DFY is the most common form of DFM – Essential for 90nm & below**
- **Physical DFY is being integrated in a modern design flow**
- **Electrical DFY is the next opportunity**
- **DFY & DFT complement each other**
- **DFM is incremental**

# Conclusions

- DFM is an extension of DFM

- Fixing Antenna and using Double cut vias in a single run:**

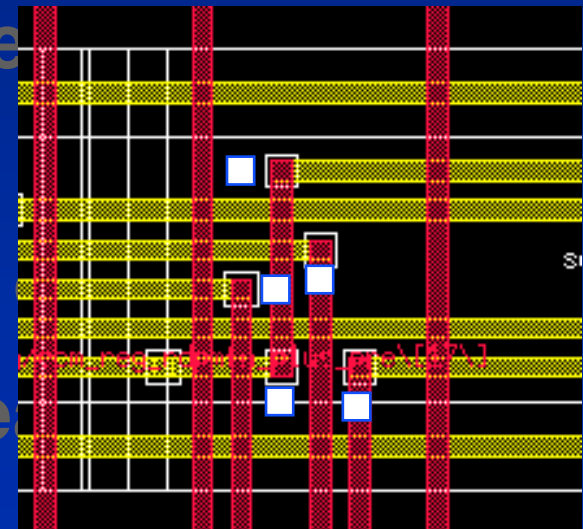
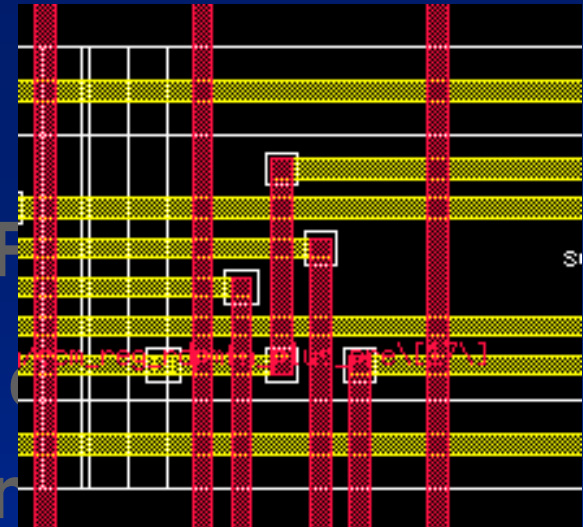
The following commands repair process antenna violations by inserting diodes and insert filler left when the diodes replace large filler cells:

```
setNanoRouteMode routeInsertAntennaDiode true
setNanoRouteMode routeAntennaCellName cell_A
setNanoRouteMode routeReInsertFillerCellList my_fillers
globalDetailRoute
```

The following commands replace single-cut vias with double-cut vias. Run these command

```
setNanoRouteMode drouteOptimizeUseMultiCutVia true
setNanoRouteMode drouteStartIteration 20
setNanoRouteMode drouteEndIteration default
detailRoute
setNanoRouteMode drouteOptimizeUseMultiCutVia false
setNanoRouteMode drouteStartIteration 16
setNanoRouteMode drouteEndIteration 20
detailRoute
```

- DFY & DFT complement each other
- DFM is incremental**



**+1.7% Yield !**